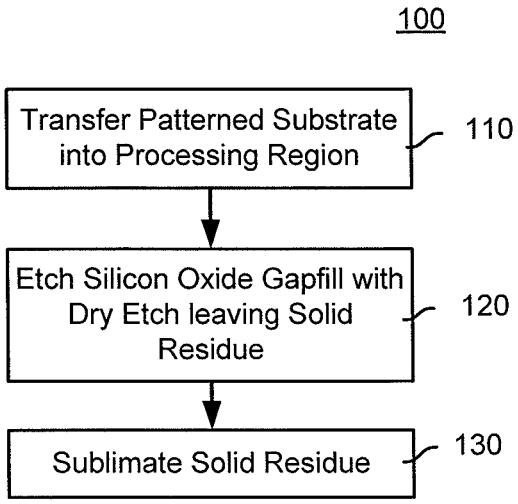


FIG. 1A
(Prior Art)

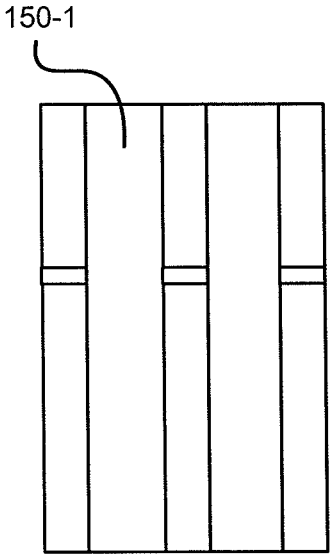


FIG. 1B
(Prior Art)

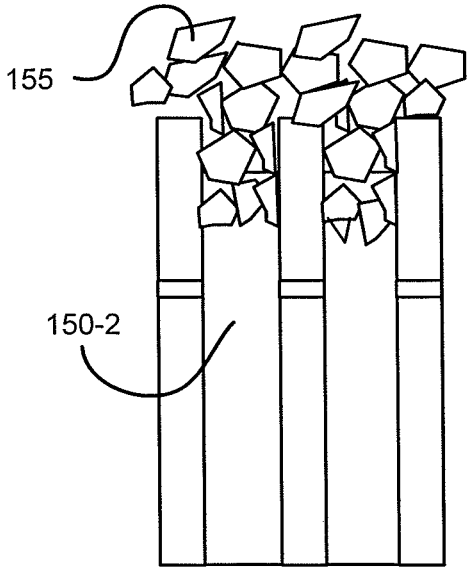


FIG. 1C
(Prior Art)

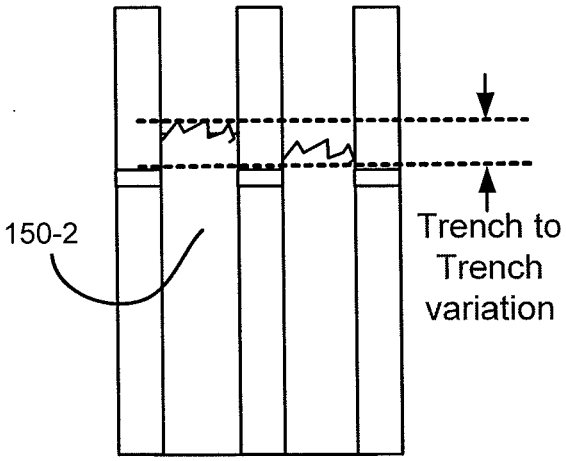


FIG. 1D
(Prior Art)

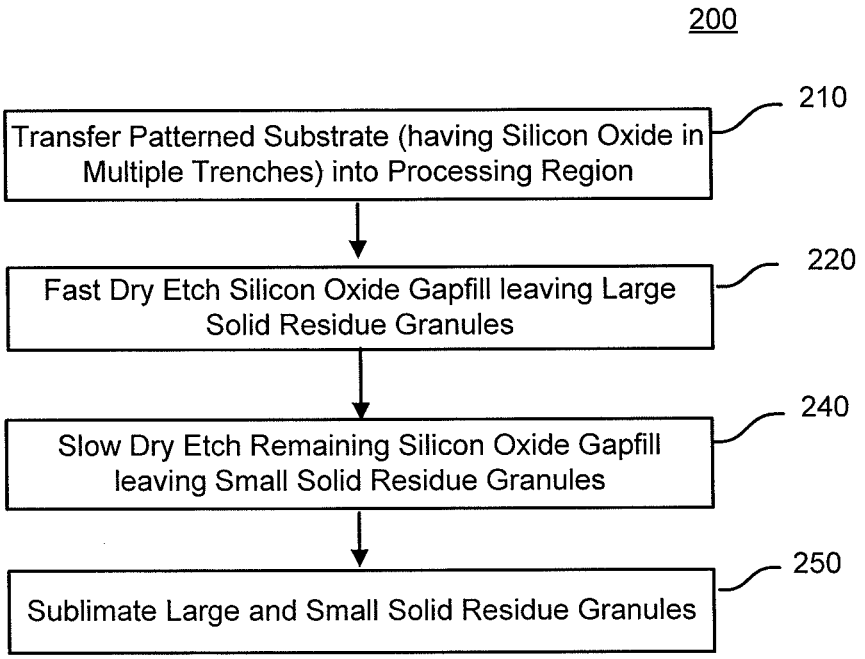

200
Transfer Patterned Substrate (having Silicon Oxide in Multiple Trenches) into Processing Region
210
Fast Dry Etch Silicon Oxide Gapfill leaving Large Solid Residue Granules
220
Slow Dry Etch Remaining Silicon Oxide Gapfill leaving Small Solid Residue Granules
240
Sublimate Large and Small Solid Residue Granules
250

FIG. 2

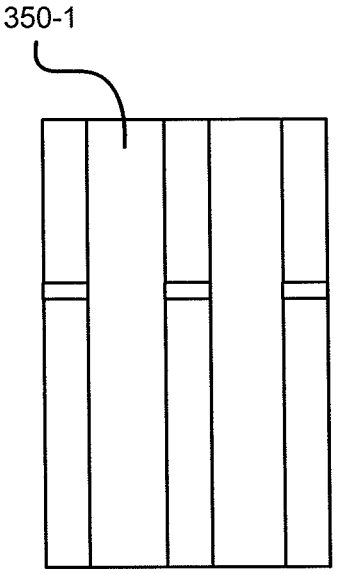


FIG. 3A

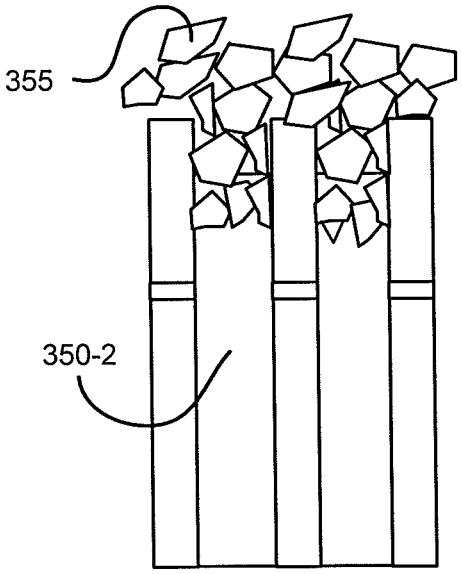


FIG. 3B

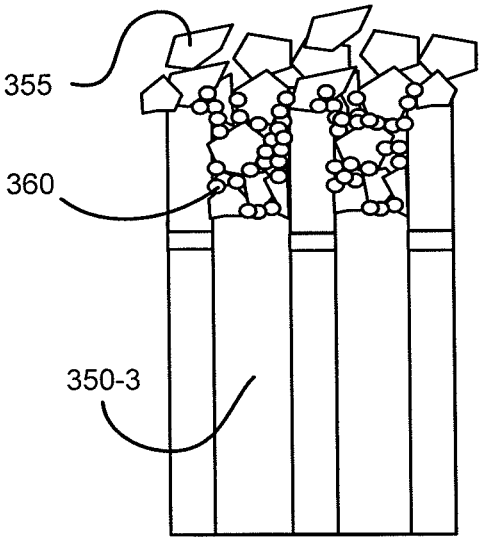


FIG. 3C

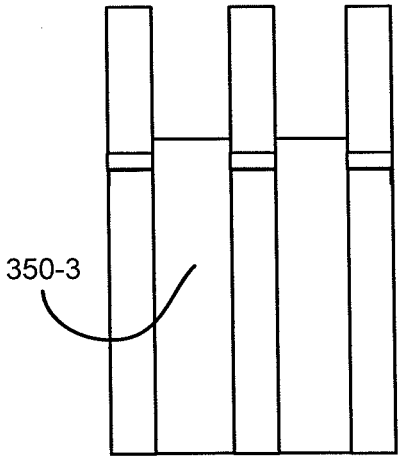


FIG. 3D

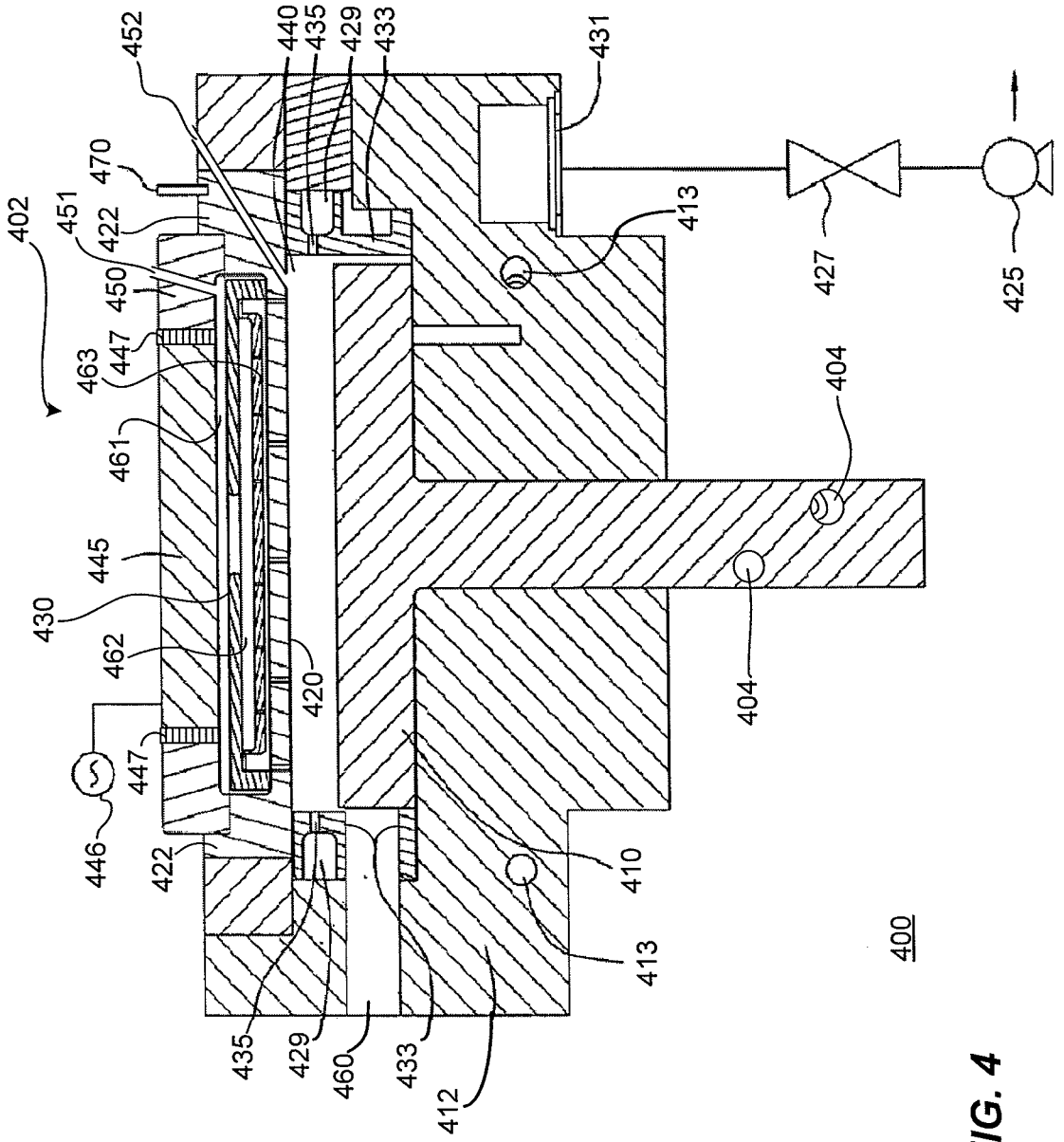

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FIG. 4

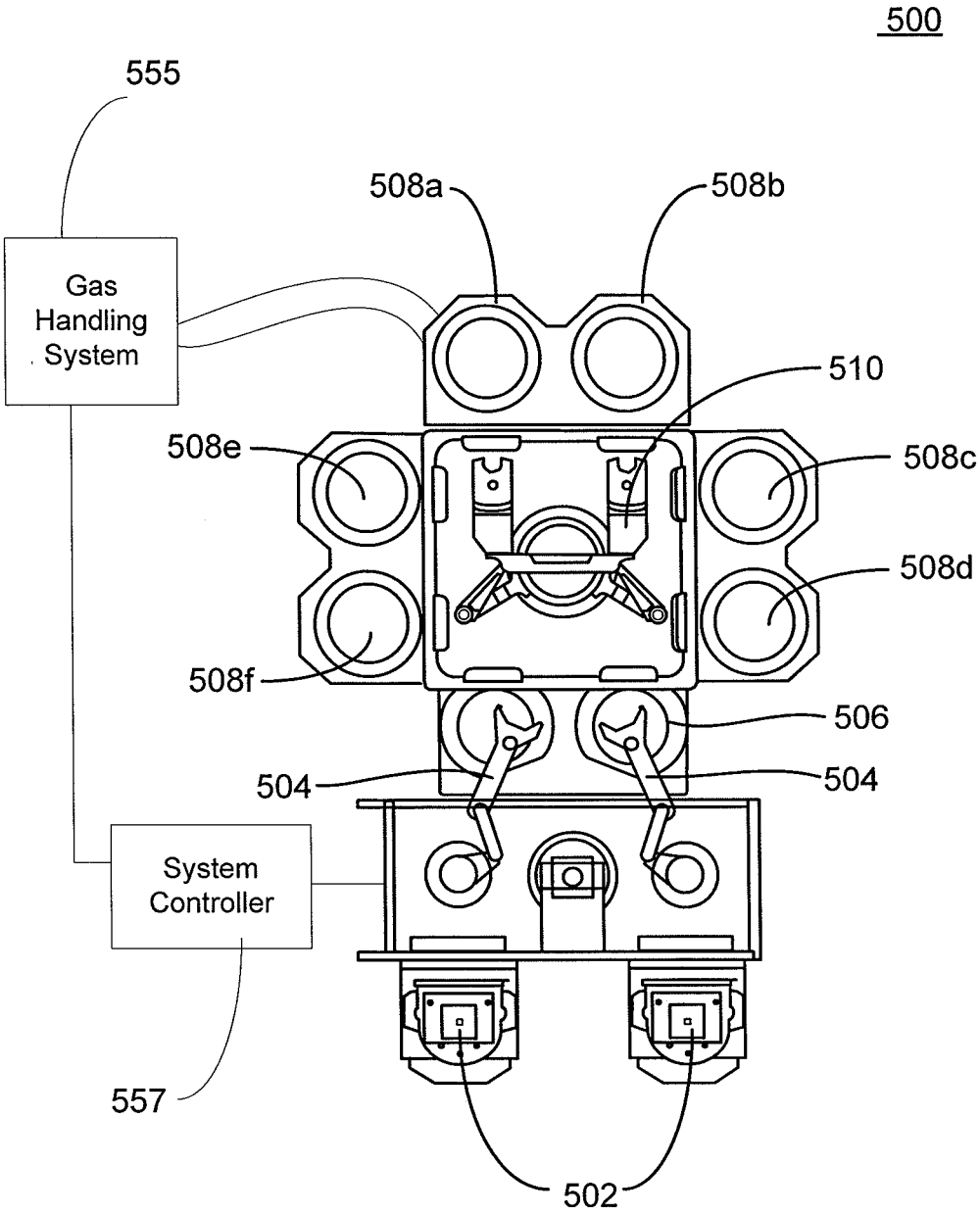

500
555
508a
508b
Gas Handling System
510
508e
508c
508d
508f
506
504
504
System Controller
557
502

FIG. 5